



**GP**  
**ELECTRONICS**

**GPM180N04LTF**  
**40V N-Channel MOSFET**

### Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	$I_D$
40V	16mΩ@10V	32A
	23mΩ@4.5V	

### Feature

- Trench Technology Power MOSFET
- Low  $R_{DS(ON)}$
- Low Gate Charge
- Low Gate Resistance
- 100% UIS Tested
- 100%  $\Delta V_{DS}$  Tested

### Application

- Power Switching Application

### MARKING:

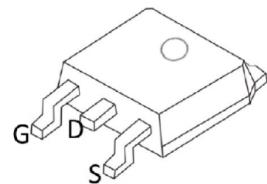


M180N04L = Device Code

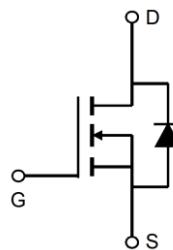
XX = Date Code

Solid Dot = Green Indicator

TO-252-2L



Schematic diagram



### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

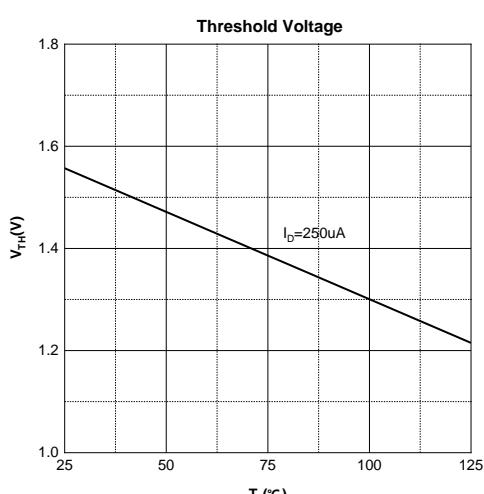
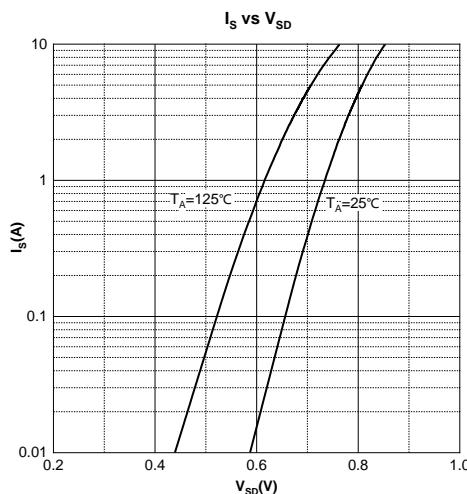
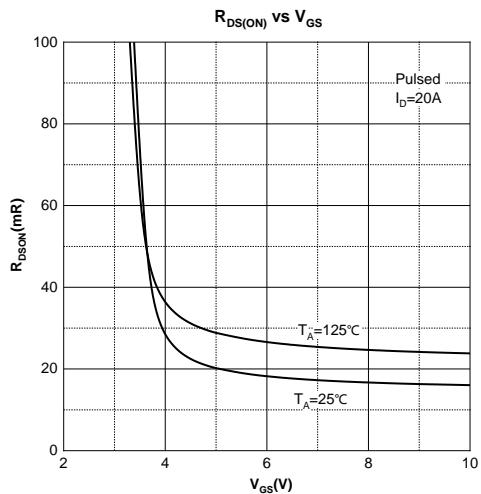
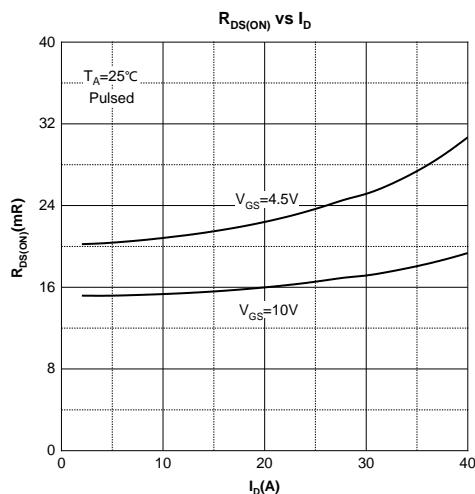
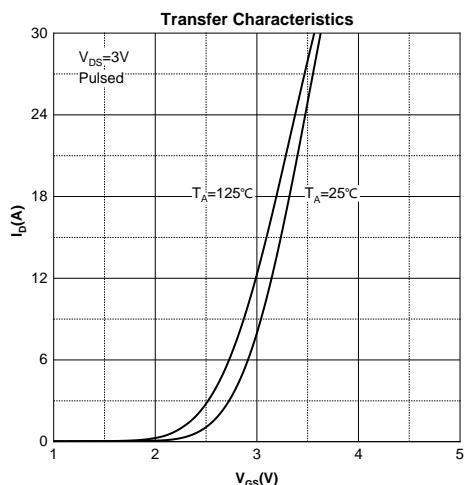
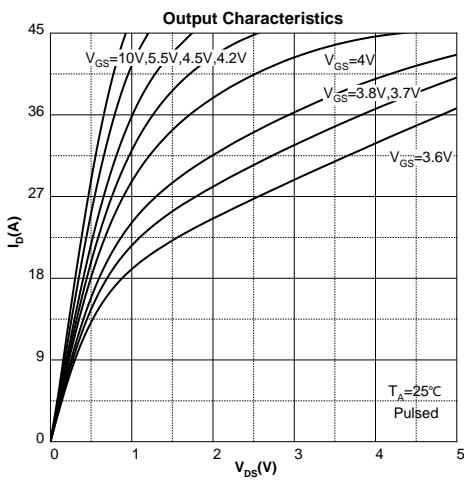
Parameter	Symbol	Value	Unit
Drain - Source Voltage	$V_{DS}$	40	V
Gate - Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current <sup>1</sup>	$I_D$	32	A
	$I_D$	21	A
Pulsed Drain Current <sup>2</sup>	$I_{DM}$	128	A
Single Pulsed Avalanche Current <sup>3</sup>	$I_{AS}$	13	A
Single Pulsed Avalanche Energy <sup>3</sup>	$E_{AS}$	42	mJ
Power Dissipation <sup>5</sup>	$P_D$	28	W
Thermal Resistance from Junction to Ambient <sup>6</sup>	$R_{\theta JA}$	52	$^\circ\text{C}/\text{W}$
Thermal Resistance from Junction to Case	$R_{\theta JC}$	4.4	$^\circ\text{C}/\text{W}$
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature	$T_{STG}$	-55~+150	$^\circ\text{C}$

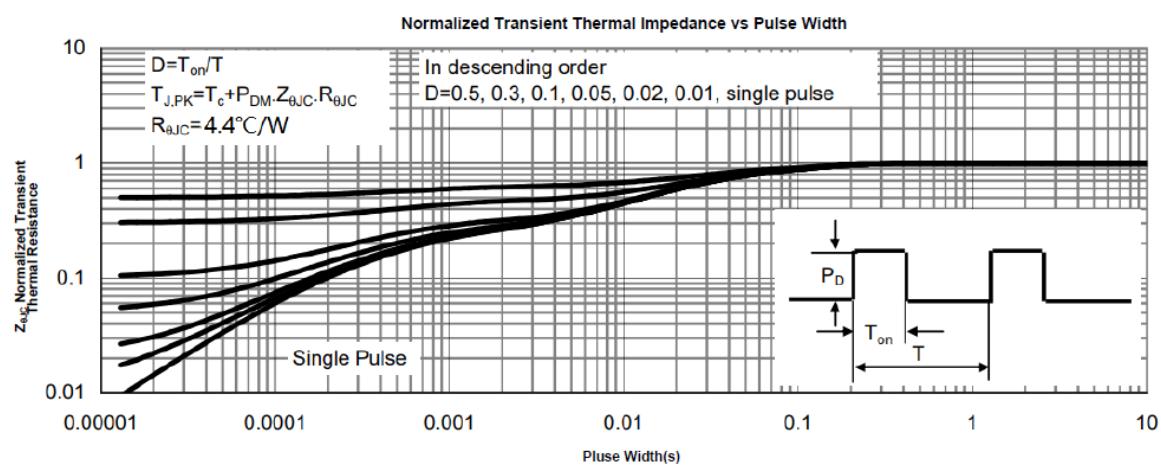
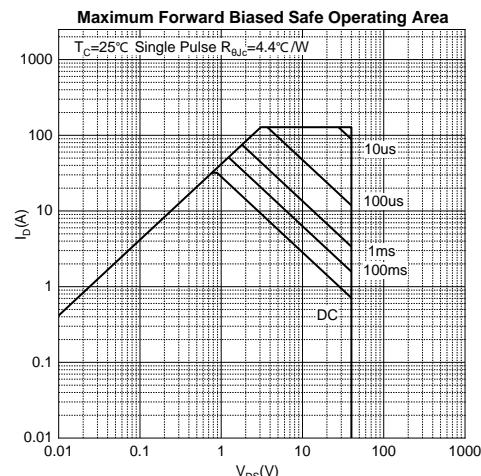
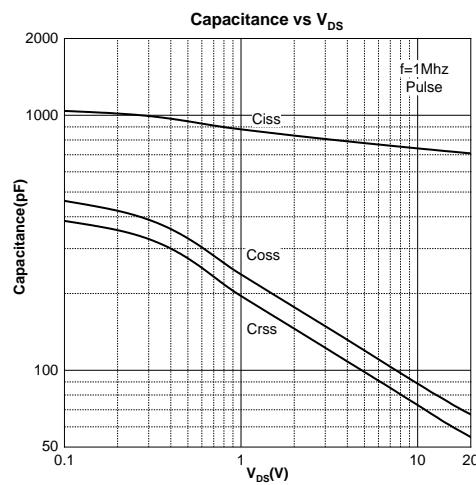
**MOSFET ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$  unless otherwise noted)**

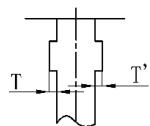
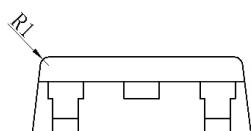
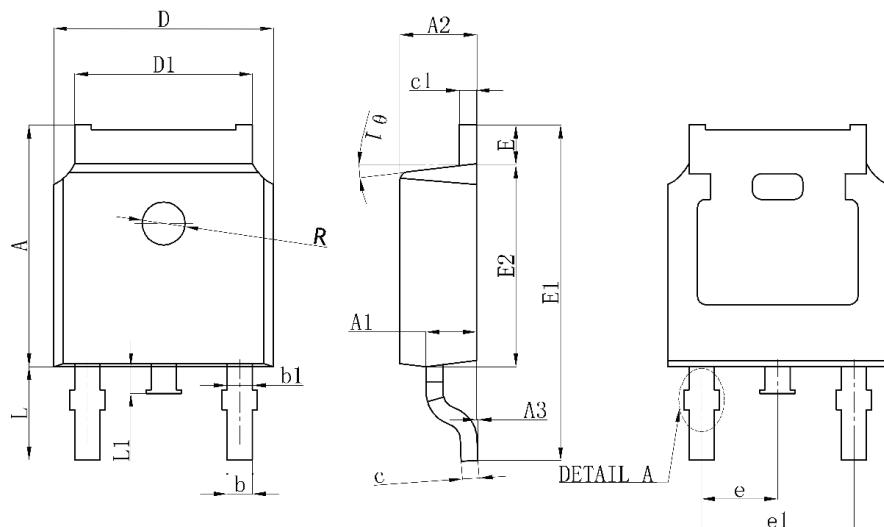
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
<b>Off Characteristics</b>						
Drain - Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{GS} = 0V, I_D = 250\mu\text{A}$	40			V
Zero Gate Voltage Drain Current	$I_{\text{DSS}}$	$V_{DS} = 40V, V_{GS} = 0V$			1	$\mu\text{A}$
Gate - Body Leakage Current	$I_{\text{GSS}}$	$V_{GS} = \pm 20V, V_{DS} = 0V$			$\pm 100$	nA
<b>On Characteristics<sup>4</sup></b>						
Gate Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	1.0	1.5	3.0	V
Drain-source On-resistance	$R_{DS(\text{on})}$	$V_{GS} = 4.5V, I_D = 9\text{A}$		16	24	$\text{m}\Omega$
		$V_{GS} = 2.5V, I_D = 5\text{A}$		23	37	
<b>Dynamic Characteristics</b>						
Input Capacitance	$C_{\text{iss}}$	$V_{DS} = 10V, V_{GS} = 0V, f = 1\text{MHz}$		2821		$\text{pF}$
Output Capacitance	$C_{\text{oss}}$			536		
Reverse Transfer Capacitance	$C_{\text{rss}}$			501		
Gate Resistance	$R_g$	$V_{DS} = 0V, V_{GS} = 0V, f = 1\text{MHz}$		1.8		$\Omega$
<b>Switching Characteristics</b>						
Total Gate Charge	$Q_g$	$V_{DS} = 20V, V_{GS} = 10V, I_D = 9\text{A}$		17		$\text{nC}$
Gate-source Charge	$Q_{gs}$			2.3		
Gate-drain Charge	$Q_{gd}$			4.2		
Turn-on Delay Time	$t_{d(\text{on})}$	$V_{DD} = 20V, V_{GS} = 10V, R_L = 1\Omega, R_G = 3\Omega$		15		$\text{ns}$
Turn-on Rise Time	$t_r$			60		
Turn-off Delay Time	$t_{d(\text{off})}$			31		
Turn-off Fall Time	$t_f$			74		
<b>Source - Drain Diode Characteristics</b>						
Diode Forward Voltage <sup>4</sup>	$V_{SD}$	$V_{GS} = 0V, I_S = 10\text{A}$			1.2	V

Notes :

- 1.The maximum current rating is limited by package.And device mounted on a large heatsink
- 2.Pulse Test : Pulse Width  $\leq 10\mu\text{s}$ , duty cycle  $\leq 1\%$ .
- 3.E<sub>AS</sub> condition:  $V_{DD} = 20V, V_{GS} = 10V, L = 0.5\text{mH}, R_G = 25\Omega$  Starting  $T_J = 25^\circ\text{C}$ .
- 4.Pulse Test : Pulse Width  $\leq 300\mu\text{s}$ , duty cycle  $\leq 2\%$ .
- 5.The power dissipation  $P_D$  is limited by  $T_{J(\text{MAX})} = 150^\circ\text{C}$ .And device mounted on a large heatsink
- 6.Device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A = 25^\circ\text{C}$ .

**Typical Characteristics**




**TO-252-2L Package Information**


$0 \leq T, T' \leq 0.12$   
DETAIL A

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	7.050	7.150	0.278	0.281
A1	0.960	1.060	0.038	0.042
A2	2.200	2.400	0.087	0.094
A3	0.000	0.100	0.000	0.004
b	0.760REF		0.030REF	
b1	1.000REF		0.039REF	
c	0.508REF		0.020REF	
c1	0.508REF		0.020REF	
D	6.550	6.650	0.258	0.262
D1	5.100	5.460	0.201	0.215
E	0.950	1.050	0.037	0.041
E1	9.700	10.400	0.382	0.409
E2	6.000	6.200	0.236	0.244
e	2.286BSC		0.090BSC	
e1	4.572REF		0.180REF	
L	2.650	2.950	0.104	0.116
L1	0.700	0.900	0.028	0.035
θ1	7°REF		7°REF	
R	1.300REF		0.051REF	
R1	0.250REF		0.010REF	